MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TPH4R10ANL

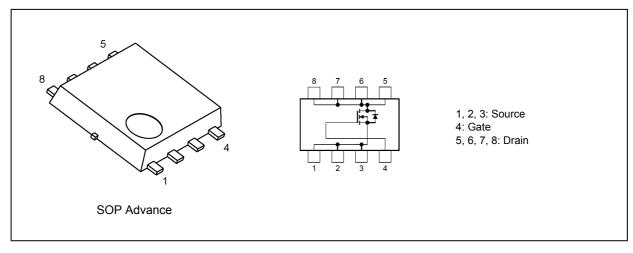
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge : $Q_{SW} = 21 \text{ nC}$ (typ.)
- (3) Small output charge : $Q_{oss} = 74 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance : $R_{DS(ON)}$ =3.3 mO (typ.)(V_{GS} = 10 V)
- (5) Low leakage current : I_{DSS} = 10 μA (max)(V_{DS} = 100 V)
- (6) Enhancement mode : V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_D = 1.0 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

| Characterist | Symbol | Rating | Unit | | |
|--------------------------------|----------------------------|--------------------|------------------|------------|----|
| Drain-source voltage | | | V _{DSS} | 100 | V |
| Gate-source voltage | | | V _{GSS} | ±20 | |
| Drain current (DC) | (T _c = 25 °C) | (Note 1) | Ι _D | 70 | A |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | Ι _D | 92 | |
| Drain current (pulsed) | (t = 100 µs) | (Note 1) | I _{DP} | 490 | |
| Power dissipation | (T _c = 25 °C) | | PD | 67 | W |
| Power dissipation | | (Note 3) | PD | 2.5 | |
| Power dissipation | | (Note 4) | PD | 0.8 | |
| Single-pulse avalanche energy | | (Note 5) | E _{AS} | 118 | mJ |
| Single-pulse avalanche current | | (Note 5) | I _{AS} | 70 | A |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | | |
|---------------------------------------|----------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance | (T _c = 25 °C) | | R _{th(ch-c)} | 1.86 | °C/W |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | (Note 3) | R _{th(ch-a)} | 50 | |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | (Note 4) | R _{th(ch-a)} | 156 | |

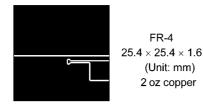
Note 1: Ensure that the channel temperature does not exceed 150 °C.

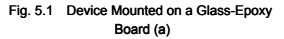
Note 2: Limited by silicon chip capability.

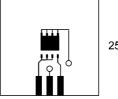
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_DD = 60 V, T_ch = 25 °C (initial), L = 26 $\mu H, \, I_{AS}$ = 70 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | V_{GS} = ±20 V, V_{DS} = 0 V | | — | ±0.1 | μA |
| Drain cut-off current | I _{DSS} | V _{DS} = 100 V, V _{GS} = 0 V | | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 100 | _ | — | V |
| Drain-source breakdown voltage (Note 6) | V _{(BR)DSX} | I _D = 10 mA, V _{GS} = -20 V | 65 | _ | _ | |
| Gate threshold voltage | V _{th} | V _{DS} = 10 V, I _D = 1.0 mA | 1.5 | _ | 2.5 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 4.5 V, I _D = 20 A | | 4.1 | 6.6 | mΩ |
| | | V _{GS} = 10 V, I _D = 35 A | | 3.3 | 4.1 | |

Note 6: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance | C _{iss} | V _{DS} = 50 V, V _{GS} = 0 V, | _ | 4850 | 6300 | pF |
| Reverse transfer capacitance | C _{rss} | f = 1 MHz | _ | 29 | 59 | |
| Output capacitance | C _{oss} | | _ | 640 | — | |
| Gate resistance | r _g | | _ | 2.1 | 3.2 | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1 | _ | 8.0 | — | ns |
| Switching time (turn-on time) | t _{on} | | _ | 20 | — | |
| Switching time (fall time) | t _f |] | | 15 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 71 | _ | |

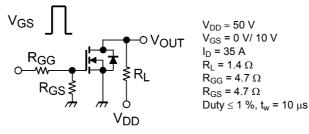


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

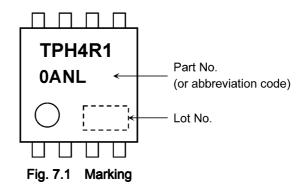
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$ $I_D = 35 \text{ A}$ | _ | 75 | _ | nC |
| | | $V_{DD} \approx 50 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ I_D = 35 A | _ | 37 | _ | |
| Gate-source charge 1 | Q _{gs1} | $V_{DD} \approx 50 \text{ V}, V_{GS} = 10 \text{ V},$ $I_D = 35 \text{ A}$ | _ | 19 | — | |
| Gate-drain charge | Q _{gd} | | _ | 12 | _ | |
| Gate switch charge | Q _{SW} | | _ | 21 | _ | |
| Output charge | Q _{oss} | V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz | | 74 | | |

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

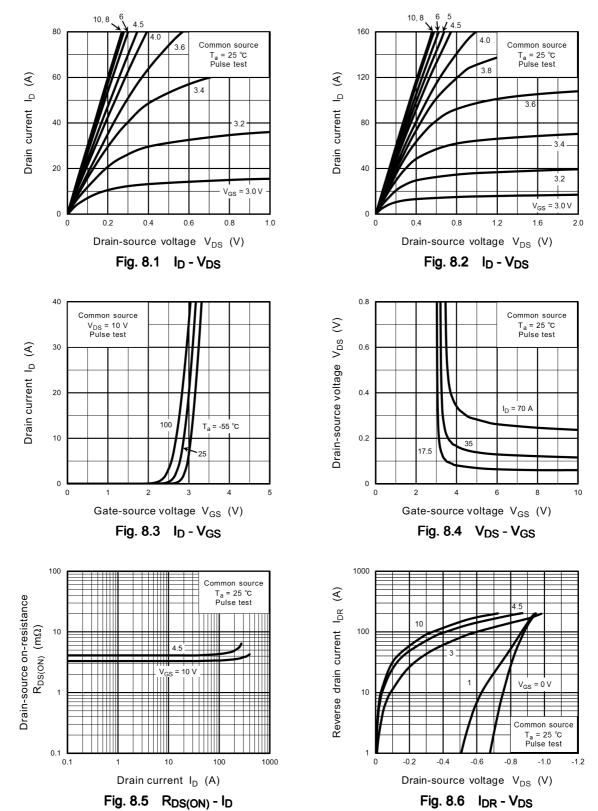
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|---------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note | ') I _{DRP} | (t = 100 µs) | _ | — | 490 | A |
| Diode forward voltage | V _{DSF} | I _{DR} = 70 A, V _{GS} = 0 V | _ | _ | -1.2 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 17.5 A, V _{GS} = 0 V, | _ | 52 | _ | ns |
| Reverse recovery charge | Q _{rr} | -dI _{DR} /dt = 100 A/μs | | 78 | _ | nC |

Note 7: Ensure that the channel temperature does not exceed 150 °C.

7. Marking



8. Characteristics Curves (Note)



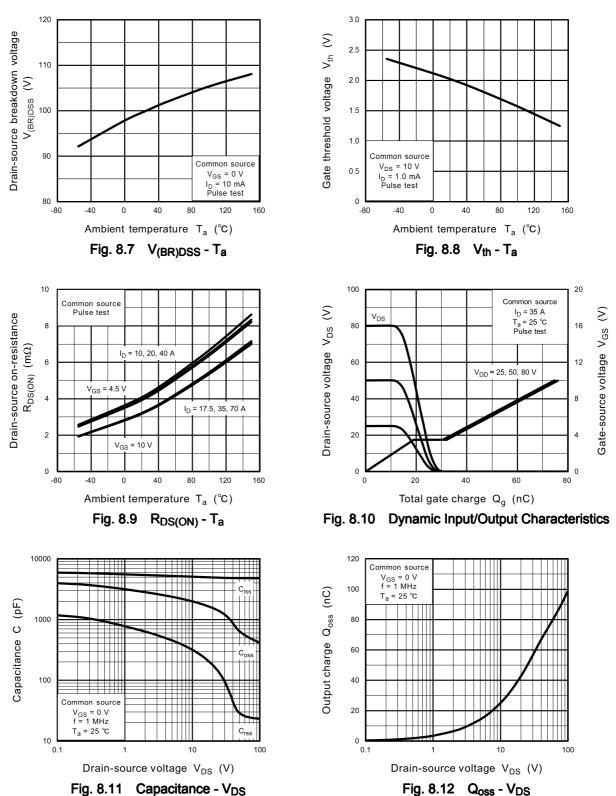
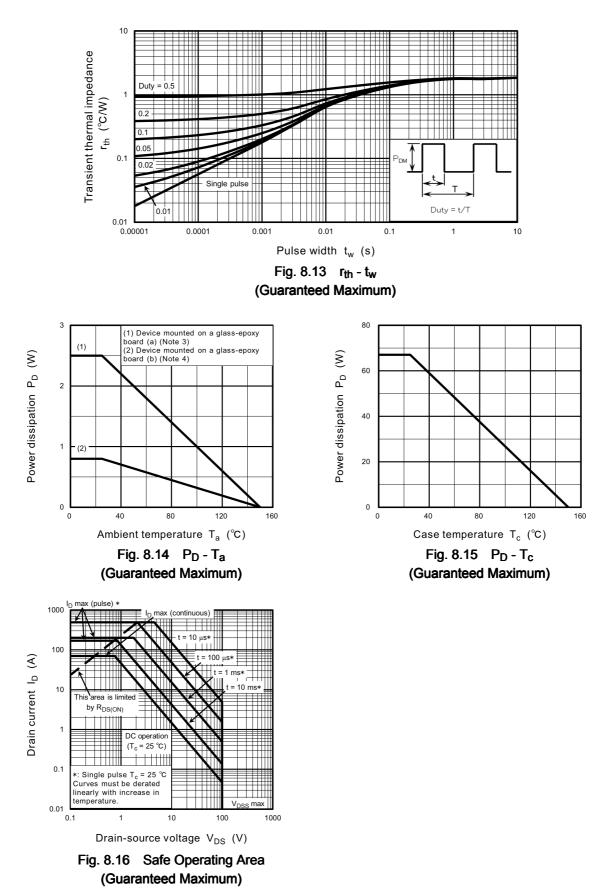


Fig. 8.11 Capacitance - VDS

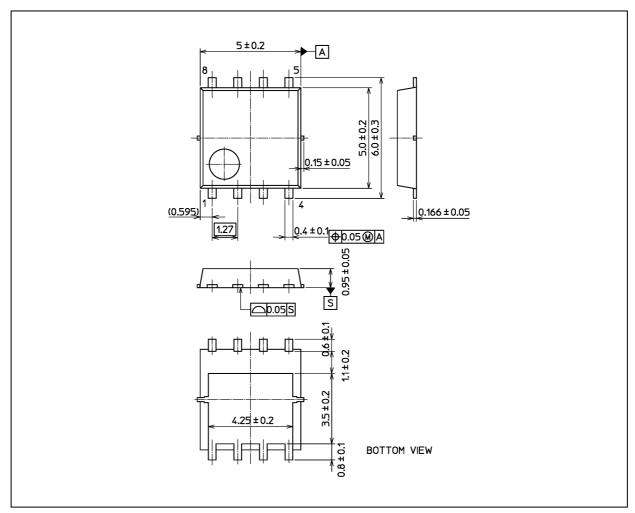


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TPH4R10ANL

Package Dimensions

Unit: mm



Weight: 0.087 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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